

Title (en)
UNIPOLAR RESISTIVE MEMORY

Title (de)
EINPOLIGER RESISTIVER SPEICHER

Title (fr)
MÉMOIRE RÉSISTIVE UNIPOLAIRE

Publication
EP 3239983 B1 20190911 (FR)

Application
EP 17165614 A 20170407

Priority
FR 1653902 A 20160429

Abstract (en)
[origin: US2017316825A1] A memory circuit including cells connected in rows and in columns, each cell including a programmable resistive element and a control transistor, the memory circuit further including a control circuit capable of, during a cell programming phase: applying a first voltage to a control conductive track of the column including the cell; applying a second voltage to the first control conductive track of the row including the cell; applying a third voltage capable of turning on the cell control transistor to a second row control conductive track including the cell; and applying a fourth voltage capable of turning off the control transistors to the control conductive tracks of columns which do not include the cell.

IPC 8 full level
G11C 13/00 (2006.01)

CPC (source: EP US)
G11C 13/0069 (2013.01 - EP US); **G11C 13/0097** (2013.01 - US); **G11C 13/0004** (2013.01 - EP US); **G11C 13/0033** (2013.01 - EP US); **G11C 2013/009** (2013.01 - EP US); **G11C 2213/79** (2013.01 - EP US); **G11C 2213/82** (2013.01 - EP US)

Designated contracting state (EPC)
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EP 17165614 A 20170407; FR 1653902 A 20160429; US 201715487303 A 20170413